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(54) **VARIABLE RESISTANCE MATERIAL AND
VARIABLE RESISTANCE MEMORY DEVICE
INCLUDING THE SAME**

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(57)

ABSTRACT

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A variable resistance memory device includes a first electrode; a variable resistance material on the first electrode; and a second electrode on the variable resistance material, wherein the variable resistance material includes an impurity (A) and is represented as $A_p\text{Ge}_x\text{Sb}_y\text{Te}_z$, an atomic concentration 'x' of the germanium is $0.4 \leq x \leq 0.5$, an atomic concentration 'z' of the tellurium is $0.3 \leq z < 0.6$, an atomic concentration 'p' of the impurity is $0 < p \leq 0.1$, and an atomic concentration 'y' of the antimony is $1-x-z-p$ and is greater than 0.

